

MOS Field Effect Transistor 2SK3366

■ Features

- Super low on-state resistance:
 $R_{DS(on)1} = 21 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 10 \text{ A)}$
 $R_{DS(on)2} = 33 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 10 \text{ A)}$
 $R_{DS(on)3} = 43 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4 \text{ V, } I_D = 10 \text{ A)}$
- Low C_{iss} : $C_{iss} = 730 \text{ pF TYP.}$
- Built-in gate protection diode

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit | |
|-------------------------|------------|------------------------|------------------|---|
| Drain to source voltage | V_{DS} | 30 | V | |
| Gate to source voltage | V_{GS} | ± 20 | V | |
| Drain current | I_D | ± 30 | A | |
| | I_{DP}^* | ± 80 | A | |
| Power dissipation | P_D | $T_A=25^\circ\text{C}$ | 1.0 | W |
| | | $T_C=25^\circ\text{C}$ | 30 | |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ | |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ | |

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|-------------------------------------|---------------|--|-----|------|----------|------------------|
| Drain cut-off current | I_{DSS} | $V_{DS}=30\text{V}, V_{GS}=0$ | | | 10 | μA |
| Gate leakage current | I_{GSS} | $V_{GS}=\pm 20\text{V}, V_{DS}=0$ | | | ± 10 | μA |
| Gate cutoff voltage | $V_{GS(off)}$ | $V_{DS}=10\text{V}, I_D=1\text{mA}$ | 1.5 | 2.0 | 2.5 | V |
| Forward transfer admittance | $ Y_{fs} $ | $V_{DS}=10\text{V}, I_D=10\text{A}$ | 5 | 10 | | S |
| Drain to source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}, I_D=10\text{A}$ | | 17.2 | 21 | $\text{m}\Omega$ |
| | | $V_{GS}=4.5\text{V}, I_D=10\text{A}$ | | 26 | 33 | $\text{m}\Omega$ |
| | | $V_{GS}=4.0\text{V}, I_D=10\text{A}$ | | 33 | 43 | $\text{m}\Omega$ |
| Input capacitance | C_{iss} | $V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$ | | 730 | | pF |
| Output capacitance | C_{oss} | | | 250 | | pF |
| Reverse transfer capacitance | C_{rss} | | | 120 | | pF |
| Turn-on delay time | t_{on} | | | 28 | | ns |
| Rise time | t_r | $I_D=10\text{A}, V_{GS(on)}=10\text{V}, R_G=10\Omega, V_{DD}=15\text{V}$ | | 420 | | ns |
| Turn-off delay time | t_{off} | | | 47 | | ns |
| Fall time | t_f | | | 64 | | ns |
| Total Gate Charge | Q_G | $V_{DD} = 24\text{V}, V_{GS} = 10 \text{ V, } I_D = 20\text{A}$ | | 15 | | nC |
| Gate to Source Charge | Q_{GS} | | | 2.8 | | nC |
| Gate to Drain Charge | Q_{GD} | | | 4.1 | | nC |

